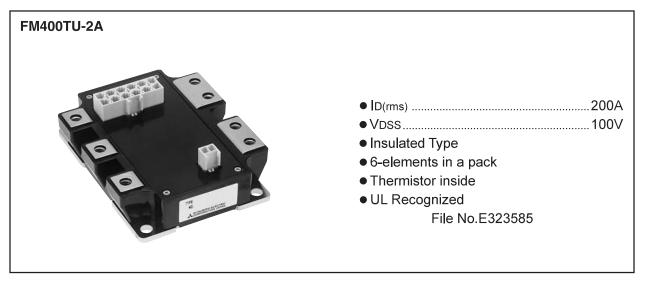
MITSUBISHI <MOSFET MODULE>

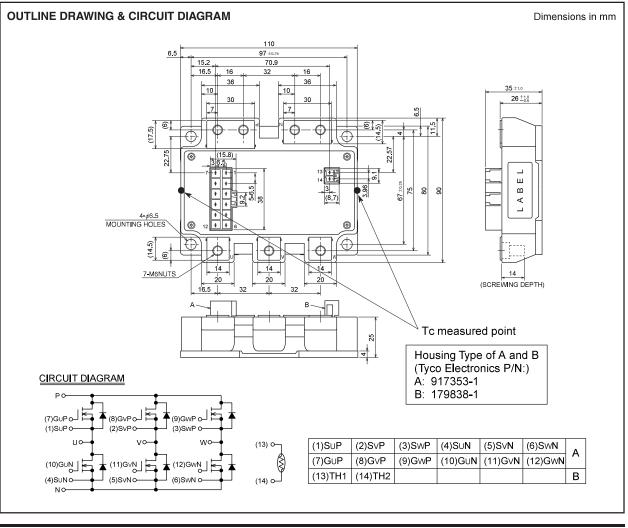
FM400TU-2A

HIGH POWER SWITCHING USE INSULATED PACKAGE



### APPLICATION

AC motor control of forklift (battery power source), UPS



### **HIGH POWER SWITCHING USE INSULATED PACKAGE**

Symbol	Item	Conditions	Rating	Unit
VDSS	Drain-source voltage	G-S Short	100	V
Vgss	Gate-source voltage	D-S Short	±20	V
D	Drain ourrant	Tc' = 130°C* <sup>3</sup>	200	A
DM	Drain current	Pulse*2	400	A
DA	Avalanche current	L = 10µH Pulse*2	200	A
IS* <sup>1</sup>	Course ourrent		200	A
SM* <sup>1</sup>	Source current	Pulse*2	400	A
PD*4	Maximum neuror discinction	Tc = 25°C	650	W
PD*4	Maximum power dissipation	$Tc' = 25^{\circ}C^{*3}$	880	W
Tch	Channel temperature		<u>    40  ~ +150  </u>	°C
Tstg	Storage temperature		<u>    40  ~ +125  </u>	°C
Visol	Isolation voltage	Main terminal to base plate, AC 1 min, f=60Hz, RMS	2500	V
_	Mounting torque	Main Terminal M6	3.5 ~ 4.5	N•m
		Mounting to heat sink M6	3.5 ~ 4.5	N•m
_	Weight	Typical value	600	g

### ABSOLUTE MAXIMUM RATINGS (Tj = 25°C unless otherwise specified.)

### ELECTRICAL CHARACTERISTICS (Tj = 25°C unless otherwise specified.)

Symbol	Item	Conditions		Limits			Unit
				Min.	Тур.	Max.	
DSS	Drain cutoff current	VDS = VDSS, VGS = 0V		—	_	1	mA
VGS(th)	Gate-source threshold voltage	ID = 20mA, VDS = 10V		4.7	6	7.3	V
GSS	Gate leakage current	VGS = VGSS, VDS = 0V		_	_	1.5	μA
<b>r</b> DS(on)	Static drain-source	ID = 200A Tj = 25°C		—	1.45	2.0	
(chip)	On-state resistance	VGS = 15V	Tj = 125°C	—	2.5	_	mΩ
VDS(on)	Static drain-source	ID = 200A	Tj = 25°C	_	0.29	0.40	V
(chip)	On-state voltage	VGS = 15V	Tj = 125°C	—	0.50	—	
RDD'-SS'	Internal lead resistance	ID = 200A	Tj = 25°C	_	0.8	_	mΩ
KDD-55		terminal-chip	Tj = 125°C	_	1.12	_	
Ciss	Input capacitance	Vps = 10V		_	_	75	
Coss	Output capacitance	VDS = 10V VGS = 0V		_	_	10	nF
Crss	Reverse transfer capacitance			_	_	6	
QG	Total gate charge	VDD = 48V, ID = 200A, VGS = 15V		_	1200	_	nC
<b>t</b> d(on)	Turn-on delay time	VDD = 48V, ID = 200A, VGS1 = VGS2 = 15V RG = $6.3\Omega$ , Inductive load switching operation IS = 200A		_	_	400	- ns
tr	Rise time			_	—	400	
td(off)	Turn-off delay time				_	450	
tf	Fall time			_	—	300	
trr* <sup>1</sup>	Reverse recovery time			_	—	250	ns
Qrr*1	Reverse recovery charge				6.0	_	μC
Vsd*1	Source-drain voltage	Is = 200A, VGS = 0V		_	_	1.3	V
Rth(j-c)	Thermal resistance	MOSFET part (1/6 module)* <sup>7</sup>		_	_	0.19	κ/w
Rth(j-c')		MOSFET part (1/6 module)* <sup>3</sup>		_	_	0.142	
Rth(c-s)	Contact thermal resistance Case to fin, Thermal grease Applied* <sup>8</sup> (1/6 module) Case to fin, Thermal grease Applied* <sup>3</sup> , * <sup>8</sup> (1/6 module)		_	0.1	_		
Rth(c'-s')			_	0.09	_		

### NTC THERMISTOR PART

Symbol	Parameter	Conditions	Limits			Linit
			Min.	Тур.	Max.	Unit
R25* <sup>6</sup>	Resistance	Ттн = 25°С* <sup>5</sup>		100	_	kΩ
B* <sup>6</sup>	B Constant	Resistance at T⊤н = 25°C, 50°C* <sup>5</sup>	_	4000	_	К

\*1: It is characteristics of the anti-parallel, source to drain free-wheel diode (FWDi).

\*2: Pulse width and repetition rate should be such that the device junction temperature (Tj) does not exceed Tj max rating.

\*3: TC' measured point is just under the chips. If use this value, Rth(s-a) should be measured just under the chips.
\*4: Pulse width and repetition rate should be such as to cause negligible temperature rise.

\*5: TTH is thermistor temperature.

\*6: B = (InR1-InR2)/(1/T1-1/T2) R1: Resistance at T1(K), R2: Resistance at T2(K)

\*7: Tc measured point is shown in page OUTLINE DRAWING. \*8: Typical value is measured by using thermally conductive grease of  $\lambda$ =0.9 W/(m·K).

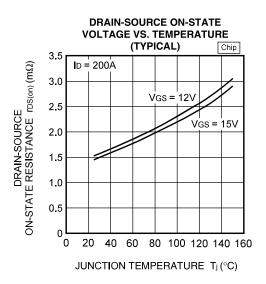


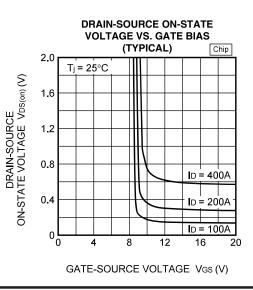
HIGH POWER SWITCHING USE INSULATED PACKAGE

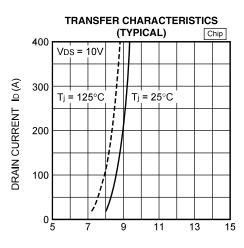
#### **OUTPUT CHARACTERISTICS** (TYPICAL) Chip 400 Vgs = 20V **'**12 350 10\ . 15∖ DRAIN CURRENT ID (A) 300 250 9V 200 150 100 50 Ti = 25°C 0 0.2 0 0.4 0.6 0.8 1.0

**PERFORMANCE CURVES** 

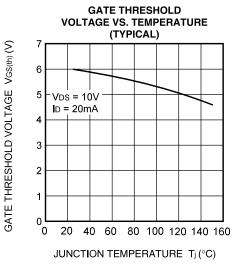
DRAIN-SOURCE VOLTAGE VDS (V)

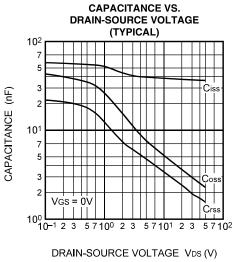






GATE-SOURCE VOLTAGE VGs (V)

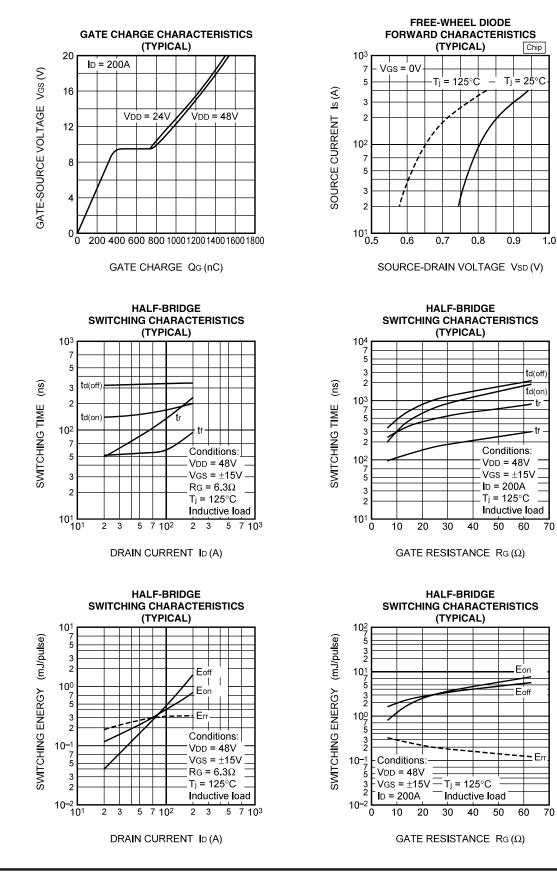




Coss

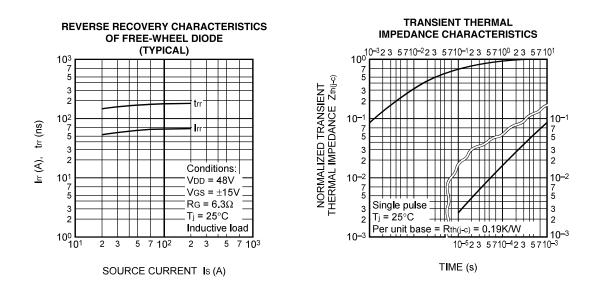


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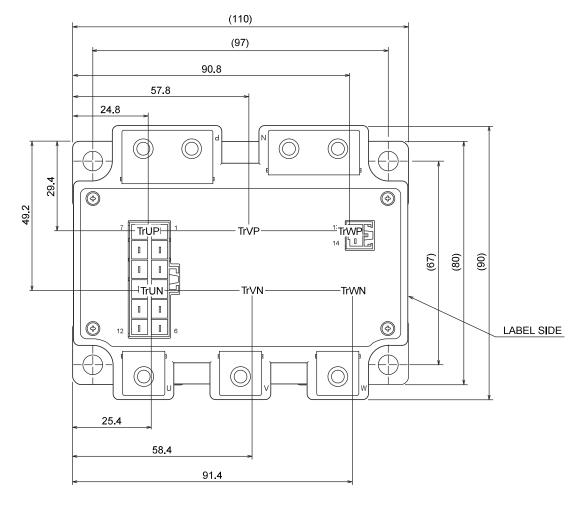




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**CHIP LAYOUT** 



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